Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

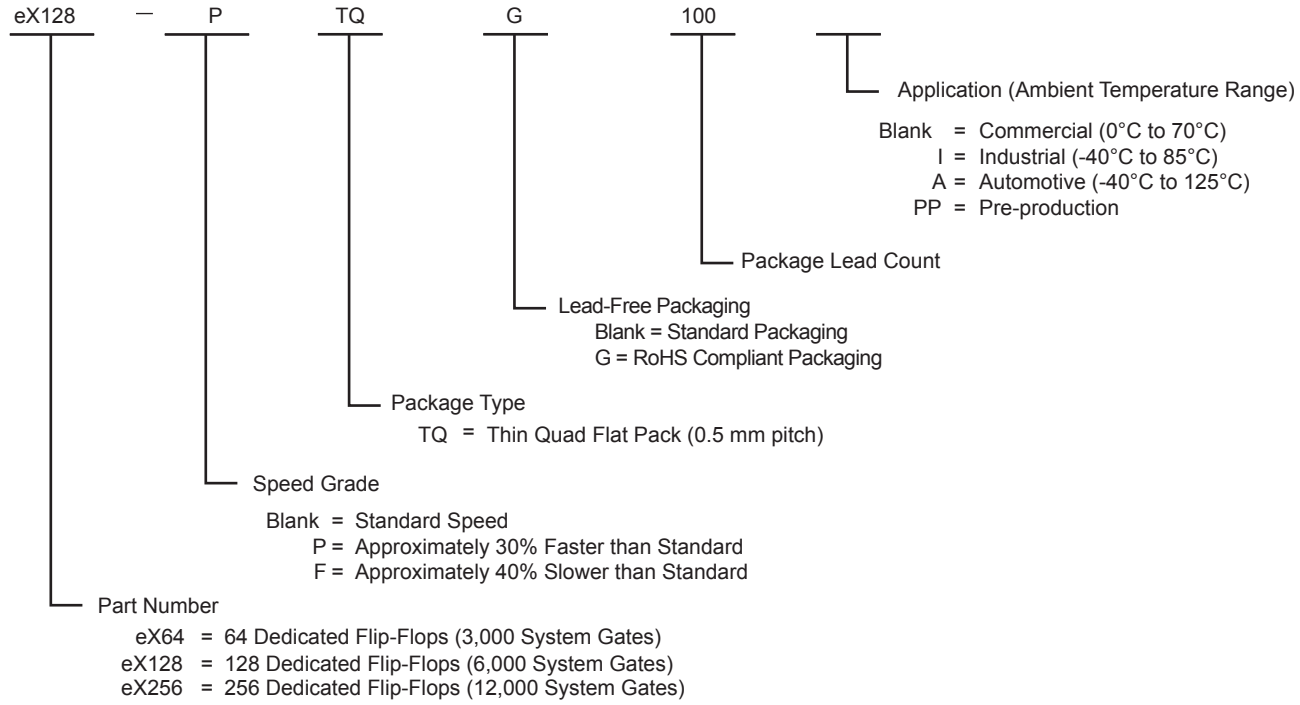
Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	512
Total RAM Bits	-
Number of I/O	81
Number of Gates	12000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	100-LQFP
Supplier Device Package	100-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/ex256-ptq100i

Ordering Information



eX Device Status

eX Devices	Status
eX64	Production
eX128	Production
eX256	Production

Plastic Device Resources

Device	User I/Os (Including Clock Buffers)	
	TQ64	TQ100
eX64	41	56
eX128	46	70
eX256	—	81

Note: TQ = Thin Quad Flat Pack

Temperature Grade Offerings

Device\ Package	TQ64	TQ100
eX64	C, I, A	C, I, A
eX128	C, I, A	C, I, A
eX256	C, I, A	C, I, A

Note: C = Commercial
I = Industrial
A = Automotive

Speed Grade and Temperature Grade Matrix

	–F	Std	–P
C	✓	✓	✓
I		✓	✓
A		✓	

Note: P = Approximately 30% faster than Standard
–F = Approximately 40% slower than Standard
Refer to the eX Automotive Family FPGAs datasheet for details on automotive temperature offerings.

Contact your local Microsemi representative for device availability.

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Routing Resources

Clusters and SuperClusters can be connected through the use of two innovative local routing resources called FastConnect and DirectConnect, which enable extremely fast and predictable interconnection of modules within Clusters and SuperClusters (Figure 1-4). This routing architecture also dramatically reduces the number of antifuses required to complete a circuit, ensuring the highest possible performance.

DirectConnect is a horizontal routing resource that provides connections from a C-cell to its neighboring R-cell in a given SuperCluster. DirectConnect uses a hard-wired signal path requiring no programmable interconnection to achieve its fast signal propagation time of less than 0.1 ns (–P speed grade).

FastConnect enables horizontal routing between any two logic modules within a given SuperCluster and vertical routing with the SuperCluster immediately below it. Only one programmable connection is used in a FastConnect path, delivering maximum pin-to-pin propagation of 0.3 ns (–P speed grade).

In addition to DirectConnect and FastConnect, the architecture makes use of two globally oriented routing resources known as segmented routing and high-drive routing. The segmented routing structure of Microsemi provides a variety of track lengths for extremely fast routing between SuperClusters. The exact combination of track lengths and antifuses within each path is chosen by the fully automatic place-and-route software to minimize signal propagation delays.

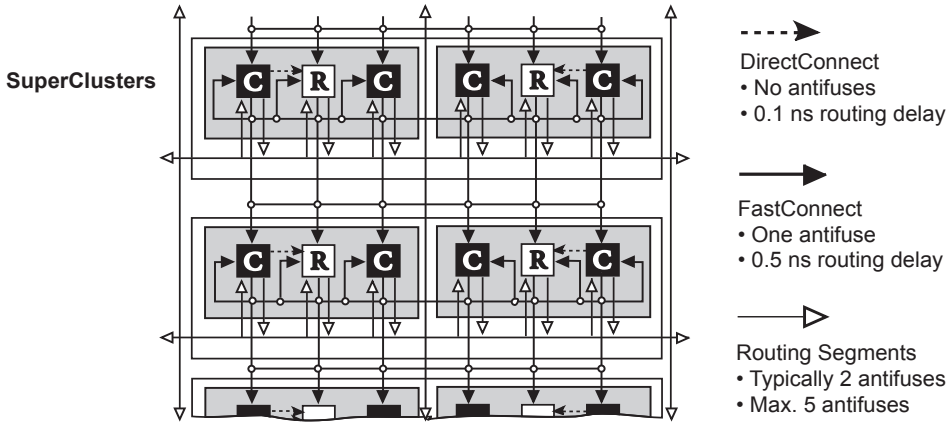


Figure 1-4 • **DirectConnect and FastConnect for SuperClusters**

Clock Resources

eX's high-drive routing structure provides three clock networks. The first clock, called HCLK, is hardwired from the HCLK buffer to the clock select MUX in each R-Cell. HCLK cannot be connected to combinational logic. This provides a fast propagation path for the clock signal, enabling the 3.9 ns clock-to-out (pad-to-pad) performance of the eX devices. The hard-wired clock is tuned to provide a clock skew of less than 0.1 ns worst case. If not used, the HCLK pin must be tied LOW or HIGH and must not be left floating. Figure 1-5 describes the clock circuit used for the constant load HCLK.

HCLK does not function until the fourth clock cycle each time the device is powered up to prevent false output levels due to any possible slow power-on-reset signal and fast start-up clock circuit. To activate HCLK from the first cycle, the TRST pin must be reserved in the Design software and the pin must be tied to GND on the board. (See the "TRST, I/O Boundary Scan Reset Pin" on page 1-32).

The remaining two clocks (CLKA, CLKB) are global routed clock networks that can be sourced from external pins or from internal logic signals (via the CLKINT routed clock buffer) within the eX device. CLKA and CLKB may be connected to sequential cells or to combinational logic. If CLKA or CLKB is sourced from internal logic signals, the external clock pin cannot be used for any other input and must be tied LOW or HIGH and must not float. Figure 1-6 describes the CLKA and CLKB circuit used in eX devices.

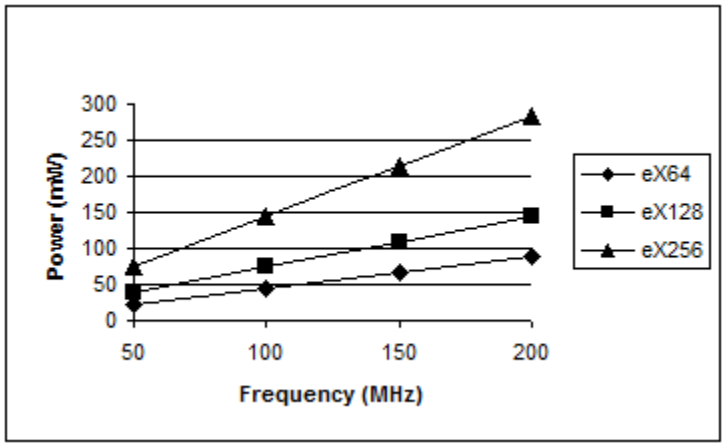
To exit the LP mode, the LP pin must be driven LOW for over 200 µs to allow for the charge pumps to power-up and device initialization can begin.

Table 1-3 illustrates the standby current of eX devices in LP mode.

Table 1-3 • **Standby Power of eX Devices in LP Mode Typical Conditions, V_{CCA}, V_{CCI} = 2.5 V, T_J = 25° C**

Product	Low Power Standby Current	Units
eX64	100	µA
eX128	111	µA
eX256	134	µA

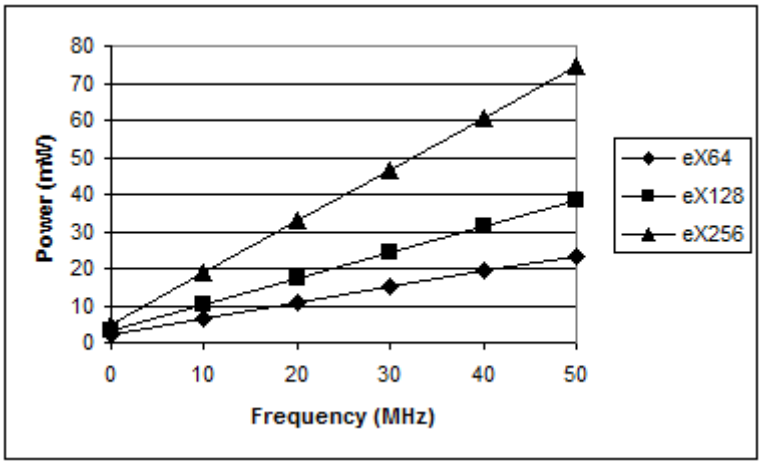
Figure 1-8 to Figure 1-11 on page 1-9 show some sample power characteristics of eX devices.



Notes:

1. *Device filled with 16-bit counters.*
2. *VCCA, VCCI = 2.7 V, device tested at room temperature.*

Figure 1-8 • **eX Dynamic Power Consumption – High Frequency**



Notes:

1. *Device filled with 16-bit counters.*
2. *VCCA, VCCI = 2.7 V, device tested at room temperature.*

Figure 1-9 • **eX Dynamic Power Consumption – Low Frequency**

3.3 V LVTTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = –8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL = 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		–10	10	–10	10	µA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		–10	10	–10	10	µA
t_R, $t_{F1,2}$	Input Transition Time			10		10	ns
C_{IO}	I/O Capacitance			10		10	pF
ICC[3,4]	Standby Current			1.5		10	mA
IV Curve	Can be derived from the IBIS model at www.microsemi.com/soc/custsup/models/ibis.html.						

Notes:

1. *t_R is the transition time from 0.8 V to 2.0 V.*
2. *t_F is the transition time from 2.0 V to 0.8 V.*
3. *ICC max Commercial –F = 5.0 mA*
4. *ICC = ICCI + ICCA*
5. *JTAG pins comply with LVTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.*

5.0 V TTL Electrical Specifications

Symbol	Parameter		Commercial		Industrial		Units
			Min.	Max.	Min.	Max.	
VOH	VCCI = MIN, VI = VIH or VIL	(IOH = –8 mA)	2.4		2.4		V
VOL	VCCI = MIN, VI = VIH or VIL	(IOL= 12 mA)		0.4		0.4	V
VIL	Input Low Voltage			0.8		0.8	V
VIH	Input High Voltage		2.0	VCCI +0.5	2.0	VCCI +0.5	V
IIL/ IIH	Input Leakage Current, VIN = VCCI or GND		–10	10	–10	10	µA
IOZ	3-State Output Leakage Current, VOUT = VCCI or GND		–10	10	–10	10	µA
t_R, $t_{F1,2}$	Input Transition Time			10		10	ns
C_{IO}	I/O Capacitance			10		10	pF
ICC[3,4]	Standby Current			15		20	mA
IV Curve	Can be derived from the IBIS model at www.microsemi.com/soc/custsup/models/ibis.html.						

Note:

1. *t_R is the transition time from 0.8 V to 2.0 V.*
2. *t_F is the transition time from 2.0 V to 0.8 V.*
3. *ICC max Commercial –F=20mA*
4. *ICC = ICCI + ICCA*
5. *JTAG pins comply with LVTTL/TTL I/O specification regardless of whether they are used as a user I/O or a JTAG I/O.*

Power Dissipation

Power consumption for eX devices can be divided into two components: static and dynamic.

Static Power Component

The power due to standby current is typically a small component of the overall power. Typical standby current for eX devices is listed in the Table 1-11 on page 1-16. For example, the typical static power for eX128 at 3.3 V V_{CCI} is:

ICC * VCCA = 795 µA x 2.5 V = 1.99 mW

Dynamic Power Component

Power dissipation in CMOS devices is usually dominated by the dynamic power dissipation. This component is frequency-dependent and a function of the logic and the external I/O. Dynamic power dissipation results from charging internal chip capacitance due to PC board traces and load device inputs. An additional component of the dynamic power dissipation is the totem pole current in the CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent dynamic power dissipation.

Dynamic power dissipation = CEQ * $VCCA^2$ x F

where:

CEQ = Equivalent capacitance

F = switching frequency

Equivalent capacitance is calculated by measuring ICCA at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency-independent, so the results can be used over a wide range of operating conditions. Equivalent capacitance values are shown below.

CEQ Values for eX Devices

Combinatorial modules (Ceqcm)	1.70 pF
Sequential modules (Ceqsm)	1.70 pF
Input buffers (Ceqi)	1.30 pF
Output buffers (Ceqo)	7.40 pF
Routed array clocks (Ceqcr)	1.05 pF

The variable and fixed capacitance of other device components must also be taken into account when estimating the dynamic power dissipation.

Table 1-12 shows the capacitance of the clock components of eX devices.

***Table 1-12* • Capacitance of Clock Components of eX Devices**

	eX64	eX128	eX256
Dedicated array clock – variable (Ceqhv)	0.85 pF	0.85 pF	0.85 pF
Dedicated array clock – fixed (Ceqhf)	18.00 pF	20.00 pF	25.00 pF
Routed array clock A (r1)	23.00 pF	28.00 pF	35.00 pF
Routed array clock B (r2)	23.00 pF	28.00 pF	35.00 pF

The estimation of the dynamic power dissipation is a piece-wise linear summation of the power dissipation of each component.

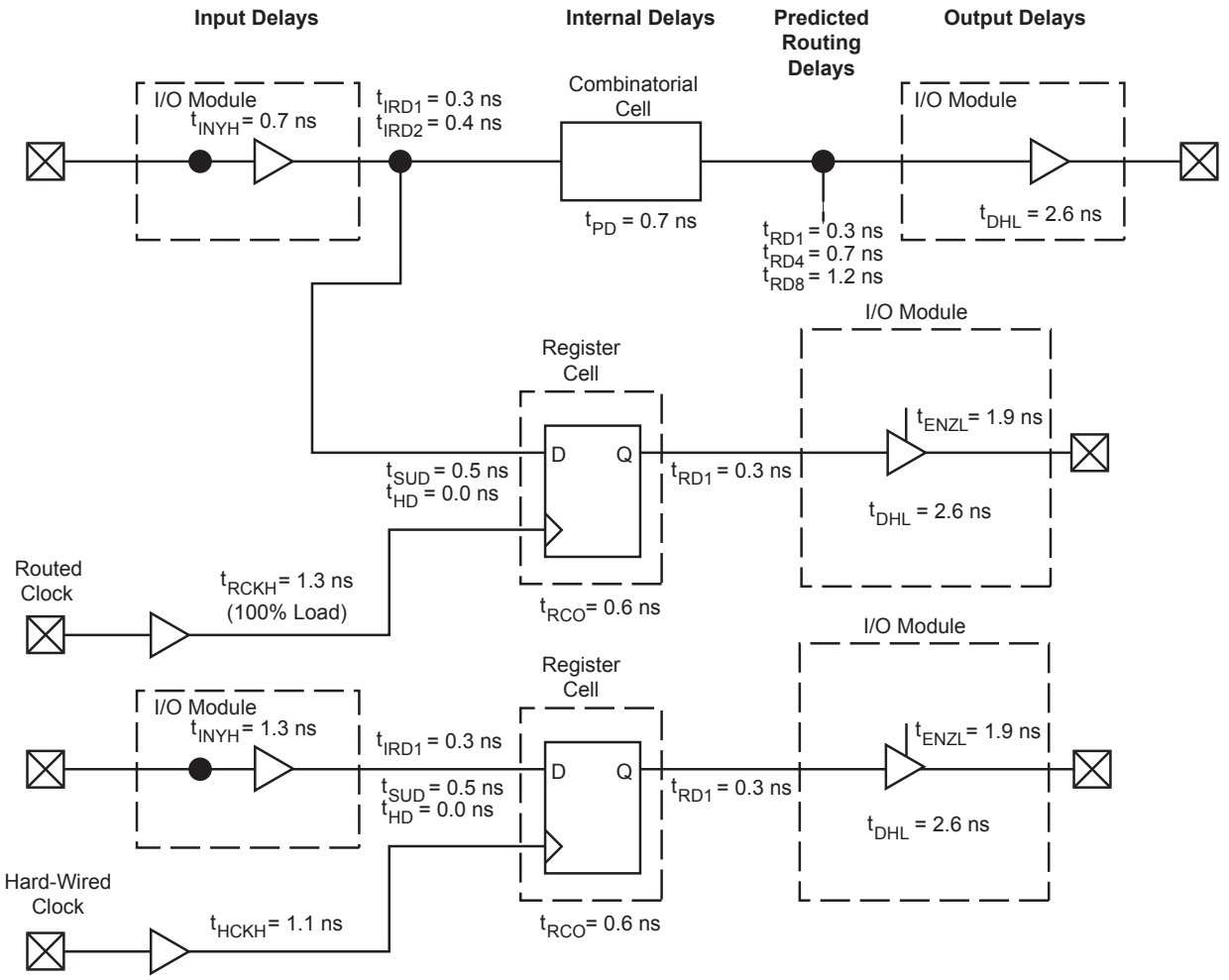
$$\text{Dynamic power dissipation} = VCCA^2 * [(m_c * C_{eqcm} * fm_C)_{\text{Comb Modules}} + (m_s * C_{eqsm} * fm_S)_{\text{Seq Modules}} + (n * C_{eqi} * fn)_{\text{Input Buffers}} + (0.5 * (q1 * C_{eqcr} * fq1) + (r1 * fq1))_{RCLKA} + (0.5 * (q2 * C_{eqcr} * fq2) + (r2 * fq2))_{RCLKB} + (0.5 * (s1 * C_{eqhv} * fs1)+(C_{eqhf} * fs1))_{HCLK}] + V_{CCI}^2 * [(p * (C_{eqo} + C_L) * fp)_{\text{Output Buffers}}]$$

where:

m_c = Number of combinatorial cells switching at frequency fm, typically 20% of C-cells
m_s = Number of sequential cells switching at frequency fm, typically 20% of R-cells
n = Number of input buffers switching at frequency fn, typically number of inputs / 4
p = Number of output buffers switching at frequency fp, typically number of outputs / 4
q1 = Number of R-cells driven by routed array clock A
q2 = Number of R-cells driven by routed array clock B
r1 = Fixed capacitance due to routed array clock A
r2 = Fixed capacitance due to routed array clock B
s1 = Number of R-cells driven by dedicated array clock
C_{eqcm} = Equivalent capacitance of combinatorial modules
C_{eqsm} = Equivalent capacitance of sequential modules
C_{eqi} = Equivalent capacitance of input buffers
C_{eqcr} = Equivalent capacitance of routed array clocks
C_{eqhv} = Variable capacitance of dedicated array clock
C_{eqhf} = Fixed capacitance of dedicated array clock
C_{eqo} = Equivalent capacitance of output buffers
C_L = Average output loading capacitance, typically 10 pF
fm_c = Average C-cell switching frequency, typically F/10
fm_s = Average R-cell switching frequency, typically F/10
fn = Average input buffer switching frequency, typically F/5
fp = Average output buffer switching frequency, typically F/5
fq1 = Frequency of routed clock A
fq2 = Frequency of routed clock B
fs1 = Frequency of dedicated array clock

The eX, SX-A and RTSX-S Power Calculator can be used to estimate the total power dissipation (static and dynamic) of eX devices: www.microsemi.com/soc/techdocs/calculators.aspx.

eX Timing Model



Note: Values shown for eX128–P, worst-case commercial conditions (5.0 V, 35 pF Pad Load).

Figure 1-14 • **eX Timing Model**

Hardwired Clock

External Setup = $t_{INYH} + t_{IRD1} + t_{SUD} – t_{HCKH}$

= 0.7 + 0.3 + 0.5 – 1.1 = 0.4 ns

Clock-to-Out (Pad-to-Pad), typical

= $t_{HCKH} + t_{RCO} + t_{RD1} + t_{DHL}$

= 1.1 + 0.6 + 0.3 + 2.6 = 4.6 ns

Routed Clock

External Setup = $t_{INYH} + t_{IRD2} + t_{SUD} – t_{RCKH}$

= 0.7 + 0.4 + 0.5 – 1.3= 0.3 ns

Clock-to-Out (Pad-to-Pad), typical

= $t_{RCKH} + t_{RCO} + t_{RD1} + t_{DHL}$

= 1.3+ 0.6 + 0.3 + 2.6 = 4.8 ns

Output Buffer Delays

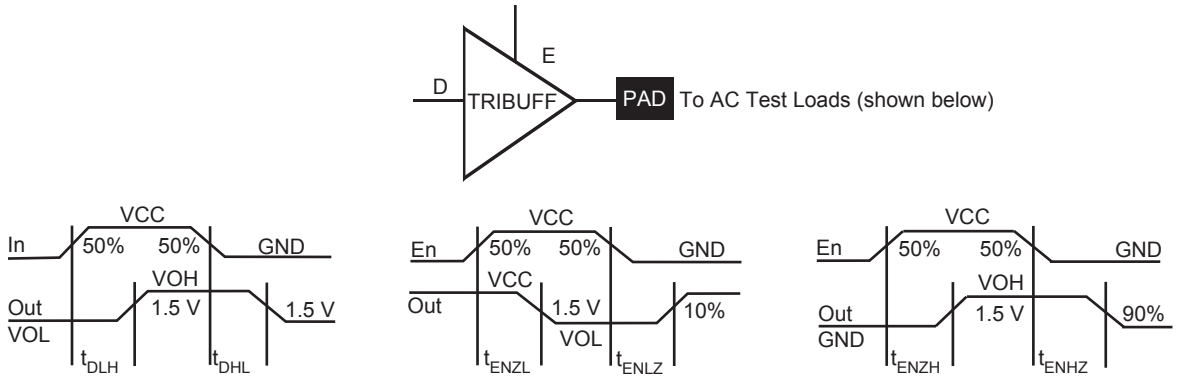


***Table 1-13* • Output Buffer Delays**

AC Test Loads

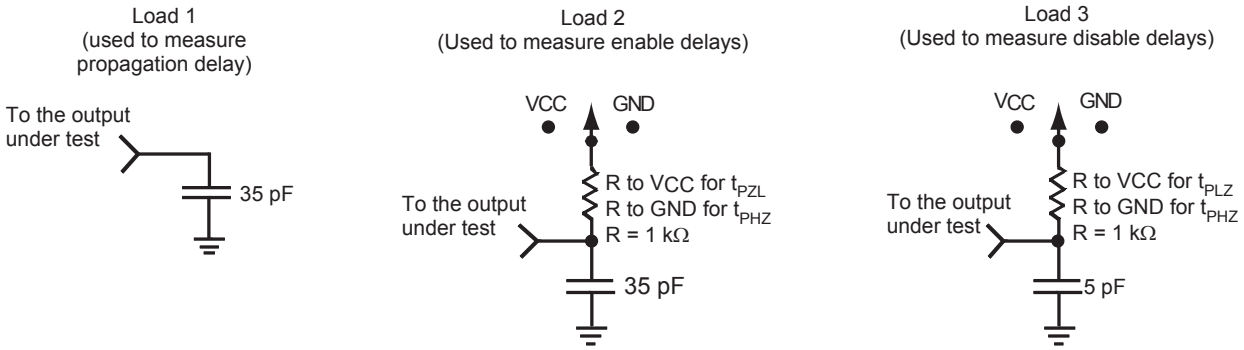


***Figure 1-15* • AC Test Loads**

Input Buffer Delays

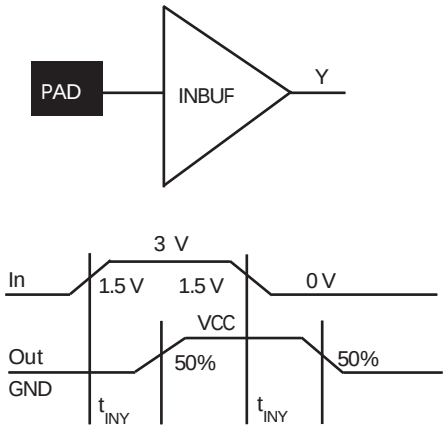


***Table 1-14* • Input Buffer Delays**

C-Cell Delays

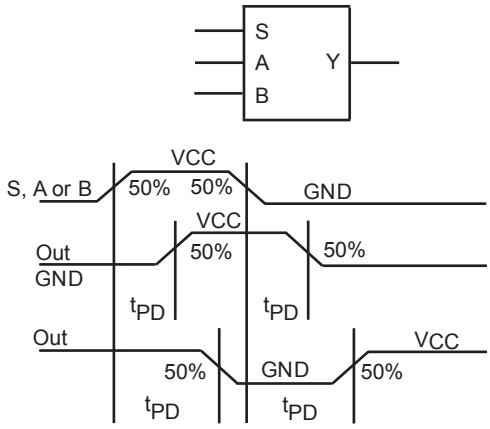


***Table 1-15* • C-Cell Delays**

eX Family Timing Characteristics

***Table 1-17* • eX Family Timing Characteristics**
(Worst-Case Commercial Conditions, VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
C-Cell Propagation Delays[1]								
t_{PD}	Internal Array Module		0.7		1.0		1.4	ns
Predicted Routing Delays[2]								
t_{DC}	FO=1 Routing Delay, DirectConnect		0.1		0.1		0.2	ns
t_{FC}	FO=1 Routing Delay, FastConnect		0.3		0.5		0.7	ns
t_{RD1}	FO=1 Routing Delay		0.3		0.5		0.7	ns
t_{RD2}	FO=2 Routing Delay		0.4		0.6		0.8	ns
t_{RD3}	FO=3 Routing Delay		0.5		0.8		1.1	ns
t_{RD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t_{RD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t_{RD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns
R-Cell Timing								
t_{RCO}	Sequential Clock-to-Q		0.6		0.9		1.3	ns
t_{CLR}	Asynchronous Clear-to-Q		0.6		0.8		1.2	ns
t_{PRESET}	Asynchronous Preset-to-Q		0.7		0.9		1.3	ns
t_{SUD}	Flip-Flop Data Input Set-Up	0.5		0.7		1.0		ns
t_{HD}	Flip-Flop Data Input Hold	0.0		0.0		0.0		ns
t_{WASYN}	Asynchronous Pulse Width	1.3		1.9		2.6		ns
$t_{RECASYN}$	Asynchronous Recovery Time	0.3		0.5		0.7		ns
t_{HASYN}	Asynchronous Hold Time	0.3		0.5		0.7		ns
2.5 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.6		0.9		1.3	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.8		1.1		1.5	ns
3.3 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
5.0 V Input Module Propagation Delays								
t_{INYH}	Input Data Pad-to-Y HIGH		0.7		1.0		1.4	ns
t_{INYL}	Input Data Pad-to-Y LOW		0.9		1.3		1.8	ns
Input Module Predicted Routing Delays[2]								
t_{IRD1}	FO=1 Routing Delay		0.3		0.4		0.5	ns
t_{IRD2}	FO=2 Routing Delay		0.4		0.6		0.8	ns
t_{IRD3}	FO=3 Routing Delay		0.5		0.8		1.1	ns
t_{IRD4}	FO=4 Routing Delay		0.7		1.0		1.3	ns
t_{IRD8}	FO=8 Routing Delay		1.2		1.7		2.4	ns
t_{IRD12}	FO=12 Routing Delay		1.7		2.5		3.5	ns

Notes:

1. *For dual-module macros, use t_{PD} + t_{RD1} + t_{PDn}, t_{RCO} + t_{RD1} + t_{PDn} or t_{PD1} + t_{RD1} + t_{SUD}, whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance.*

Table 1-19 • eX Family Timing Characteristics
(Worst-Case Commercial Conditions VCCA = 2.3V, VCCI = 2.3 V or 3.0V, T_J = 70°C)

		'–P' Speed		'Std' Speed		'–F' Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
Dedicated (Hard-Wired) Array Clock Networks								
t_{HCKH}	Input LOW to HIGH (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t_{HCKL}	Input HIGH to LOW (Pad to R-Cell Input)		1.1		1.6		2.3	ns
t_{HPWH}	Minimum Pulse Width HIGH	1.4		2.0		2.8		ns
t_{HPWL}	Minimum Pulse Width LOW	1.4		2.0		2.8		ns
t_{HCKSW}	Maximum Skew		<0.1		<0.1		<0.1	ns
t_{HP}	Minimum Period	2.8		4.0		5.6		ns
f_{HMAX}	Maximum Frequency		357		250		178	MHz
Routed Array Clock Networks								
t_{RCKH}	Input LOW to HIGH (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t_{RCKL}	Input HIGH to LOW (Light Load) (Pad to R-Cell Input) MAX.		1.0		1.4		2.0	ns
t_{RCKH}	Input LOW to HIGH (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t_{RCKL}	Input HIGH to LOW (50% Load) (Pad to R-Cell Input) MAX.		1.2		1.7		2.4	ns
t_{RCKH}	Input LOW to HIGH (100% Load) (Pad to R-Cell Input) MAX.		1.4		2.0		2.8	ns
t_{RCKL}	Input HIGH to LOW (100% Load) (Pad to R-Cell Input) MAX.		1.4		2.0		2.8	ns
t_{RPWH}	Min. Pulse Width HIGH	1.4		2.0		2.8		ns
t_{RPWL}	Min. Pulse Width LOW	1.4		2.0		2.8		ns
t_{RCKSW}*	Maximum Skew (Light Load)		0.2		0.3		0.4	ns
t_{RCKSW}*	Maximum Skew (50% Load)		0.2		0.2		0.3	ns
t_{RCKSW}*	Maximum Skew (100% Load)		0.1		0.1		0.2	ns

*Note: *Clock skew improves as the clock network becomes more heavily loaded.*

Table 1-20 • **eX Family Timing Characteristics**
(Worst-Case Commercial Conditions VCCA = 2.3 V, T_J = 70°C)

		–P Speed		Std Speed		–F Speed		
Parameter	**Description**	**Min.**	**Max.**	**Min.**	**Max.**	**Min.**	**Max.**	**Units**
2.5 V LVCMOS Output Module Timing[1] (VCCI = 2.3 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		3.3		4.7		6.6	ns
t_{DHL}	Data-to-Pad HIGH to LOW		3.5		5.0		7.0	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		11.6		16.6		23.2	ns
t_{ENZL}	Enable-to-Pad, Z to L		2.5		3.6		5.1	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		11.8		16.9		23.7	ns
t_{ENZH}	Enable-to-Pad, Z to H		3.4		4.9		6.9	ns
t_{ENLZ}	Enable-to-Pad, L to Z		2.1		3.0		4.2	ns
t_{ENHZ}	Enable-to-Pad, H to Z		2.4		5.67		7.94	ns
d_{TLH}	Delta Delay vs. Load LOW to HIGH		0.034		0.046		0.066	ns/pF
d_{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d_{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
3.3 V LVTTL Output Module Timing[1] (VCCI = 3.0 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		2.8		4.0		5.6	ns
t_{DHL}	Data-to-Pad HIGH to LOW		2.7		3.9		5.4	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		9.7		13.9		19.5	ns
t_{ENZL}	Enable-to-Pad, Z to L		2.2		3.2		4.4	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		9.7		13.9		19.6	ns
t_{ENZH}	Enable-to-Pad, Z to H		2.8		4.0		5.6	ns
t_{ENLZ}	Enable-to-Pad, L to Z		2.8		4.0		5.6	ns
t_{ENHZ}	Enable-to-Pad, H to Z		2.6		3.8		5.3	ns
d_{TLH}	Delta Delay vs. Load LOW to HIGH		0.02		0.03		0.046	ns/pF
d_{THL}	Delta Delay vs. Load HIGH to LOW		0.016		0.022		0.05	ns/pF
d_{THLS}	Delta Delay vs. Load HIGH to LOW—Low Slew		0.05		0.072		0.1	ns/pF
5.0 V TTL Output Module Timing* (VCCI = 4.75 V)								
t_{DLH}	Data-to-Pad LOW to HIGH		2.0		2.9		4.0	ns
t_{DHL}	Data-to-Pad HIGH to LOW		2.6		3.7		5.2	ns
t_{DHLS}	Data-to-Pad HIGH to LOW—Low Slew		6.8		9.7		13.6	ns
t_{ENZL}	Enable-to-Pad, Z to L		1.9		2.7		3.8	ns
t_{ENZLS}	Enable-to-Pad Z to L—Low Slew		6.8		9.8		13.7	ns
t_{ENZH}	Enable-to-Pad, Z to H		2.1		3.0		4.1	ns
t_{ENLZ}	Enable-to-Pad, L to Z		3.3		4.8		6.6	ns

*Note: *Delays based on 35 pF loading.*

TMS **Test Mode Select**

The TMS pin controls the use of the IEEE 1149.1 Boundary scan pins (TCK, TDI, TDO, TRST). In flexible mode when the TMS pin is set LOW, the TCK, TDI, and TDO pins are boundary scan pins (refer to Table 1-4 on page 1-10). Once the boundary scan pins are in test mode, they will remain in that mode until the internal boundary scan state machine reaches the “logic reset” state. At this point, the boundary scan pins will be released and will function as regular I/O pins. The “logic reset” state is reached five TCK cycles after the TMS pin is set HIGH. In dedicated test mode, TMS functions as specified in the IEEE 1149.1 specifications.

TRST, I/O **Boundary Scan Reset Pin**

Once it is configured as the JTAG Reset pin, the TRST pin functions as an active-low input to asynchronously initialize or reset the boundary scan circuit. The TRST pin is equipped with an internal pull-up resistor. This pin functions as an I/O when the **Reserve JTAG Reset** Pin is not selected in the Designer software.

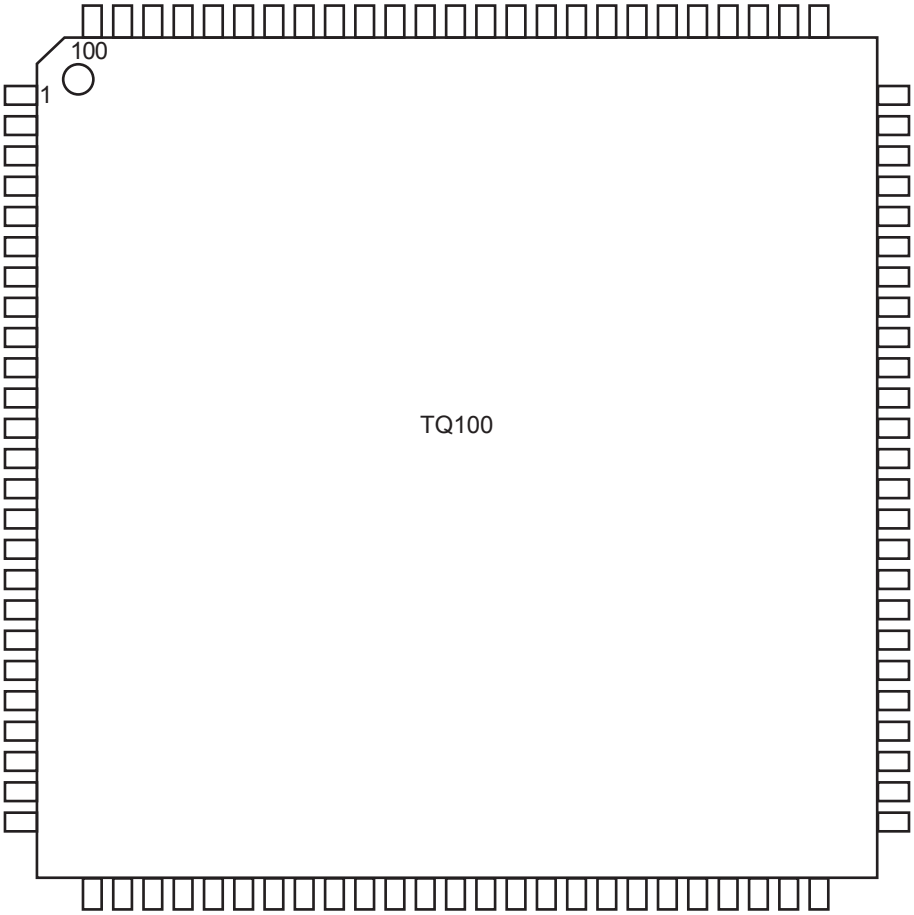
VCCI **Supply Voltage**

Supply voltage for I/Os.

VCCA **Supply Voltage**

Supply voltage for Array.

TQ100



Note: For Package Manufacturing and Environmental information, visit Resource center at www.microsemi.com/soc/products/rescenter/package/index.html.

Revision	Changes	Page
v4.0 (continued)	The "Flexible Mode" section was updated.	1-10
	Table 1-5 •Boundary-Scan Pin Configurations and Functions is new.	1-11
	The "TRST Pin" section was updated.	1-11
	The "Probing Capabilities" section is new.	1-12
	The "Programming" section was updated.	1-12
	The "Probing Capabilities" section was updated.	1-12
	The "Silicon Explorer II Probe" section was updated.	1-12
	The "Design Considerations" section was updated.	1-13
	The "Development Tool Support" section was updated.	1-13
	The "Absolute Maximum Ratings*" section was updated.	1-16
	The "Temperature and Voltage Derating Factors" section was updated.	1-26
	The "TDI, I/O Test Data Input" section was updated.	1-31
	The "TDO, I/O Test Data Output" section was updated.	1-31
	The "TMS Test Mode Select" section was updated.	1-32
	The "TRST, I/O Boundary Scan Reset Pin" section was updated.	1-32
	All VSV pins were changed to VCCA. The change affected the following pins: 64-Pin TQFP – Pin 36 100-Pin TQFP – Pin 57 49-Pin CSP – Pin D5 128-Pin CSP– Pin H11 and Pin J1 for eX256 180-Pin CSP – Pins J12 and K2	
v3.0	The "Recommended Operating Conditions" section has been changed.	1-16
	The "3.3 V LVTTL Electrical Specifications" section has been updated.	1-18
	The "5.0 V TTL Electrical Specifications" section has been updated.	1-18
	The "Total Dynamic Power (mW)" section is new.	1-9
	The "System Power at 5%, 10%, and 15% Duty Cycle" section is new.	1-9
	The "eX Timing Model" section has been updated.	1-22
v2.0.1	The I/O Features table, Table 1-2 on page 1-6, was updated.	1-6
	The table, "Standby Power of eX Devices in LP Mode Typical Conditions, VCCA, VCCI = 2.5 V, TJ = 25° C" section, was updated.	1-7
	"Typical eX Standby Current at 25°C" section is a new table.	1-16
	The table in the section, "Package Thermal Characteristics" section has been updated for the 49-Pin CSP.	1-21
	The "eX Timing Model" section has been updated.	1-22
	The timing numbers found in, "eX Family Timing Characteristics" section have been updated.	1-27
	The V_{SV} pin has been added to the "Pin Description" section.	1-31
	Please see the following pin tables for the V_{SV} pin and an important footnote including the pin: "TQ64", "TQ100", "128-Pin CSP", and "180-Pin CSP".	2-1, 2-3, 2-6, 2-11
	The figure, "TQ64" section has been updated.	2-1

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "eX Device Status" table on page II, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Production

This version contains information that is considered to be final.

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